

TRIAC (ISOLATED MOLD TYPE)

TG25C

UL:E76102(M)

SanRex Triac TG25C is isolated mold TRIAC suitable for wide range of applications like Copier Machines, Micro Wave Ovens, Solid State Switches, Motor Controls, Light Controls and Heater Controls.

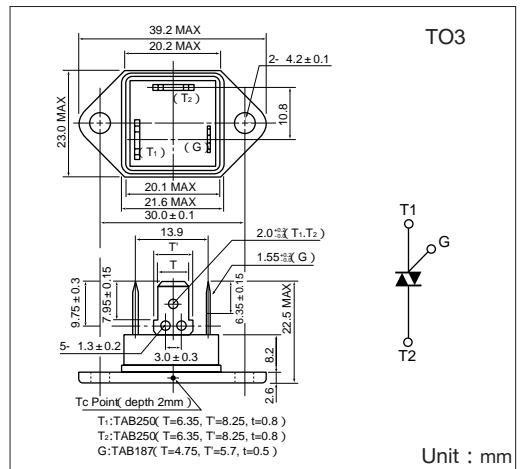
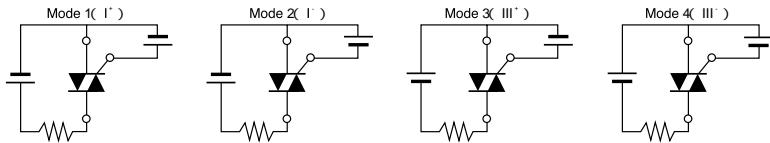
$I_{T(AV)}$ 25A

High surge capability 250A

Isolated Mounting(AC2500V)

Tab Terminals

Trigger mode of the triac



Maximum Ratings

($T_j = 25$ unless otherwise specified)

Symbol	Item	Ratings		Unit
		TG25C40	TG25C60	
V_{DRM}	Repetitive Peak Off-State Voltage	400	600	V
$I_{T(RMS)}$	R.M.S. On-State Current	25	A	
I_{TSM}	Surge On-State Current	220/250	A	
I^2t	I^2t	260	A ² S	
PGM	Peak Gate Power Dissipation	10	W	
$P_{G(AV)}$	Average Gate Power Dissipation	1	W	
I_{GM}	Peak Gate Current	3	A	
V_{GM}	Peak Gate Voltage	10	V	
di/dt	Critical Rate of Rise of On-State Current	$I_G = 100mA, T_j = 25, V_D = \frac{1}{2}V_{DRM}, dI_G/dt = 1A/\mu s$	50	A/ μs
T_j	Operating Junction Temperature	- 25 to + 125		
T_{stg}	Storage Temperature	- 40 to + 125		
V_{iso}	Isolation Breakdown Voltage (R.M.S.)	2500	V	
	Mounting Torque(M4)	1.5(15)	N·m (kgf·cm)	
	Mass	27	g	

Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max	$V_D = V_{DRM}$, Single phase, half wave, $T_j = 125$	5	mA
V_{TM}	Peak On-State Voltage, max	On-State Current [$2 \times I_{T(RMS)}$], Inst. measurement	1.4	V
I_{GT1}^+	Gate Trigger Current, max	$T_j = 25, I_T = 1A, V_D = 6V$	50	mA
I_{GT1}^-		$T_j = 25, I_T = 1A, V_D = 6V$	50	
I_{GT3}^+			-	
I_{GT3}^-		$T_j = 25, I_T = 1A, V_D = 6V$	50	
V_{GT1}^+	Gate Trigger Voltage, max	$T_j = 25, I_T = 1A, V_D = 6V$	3	V
V_{GT1}^-		$T_j = 25, I_T = 1A, V_D = 6V$	3	
V_{GT3}^+			-	
V_{GT3}^-		$T_j = 25, I_T = 1A, V_D = 6V$	3	
V_{GD}	Non-Trigger Gate Voltage, min	$T_j = 125, V_D = \frac{1}{2}V_{DRM}$	0.2	V
tgt	Turn On Time, max.	$I_{T(RMS)}, I_G = 100mA, V_D = \frac{1}{2}V_{DRM}, T_j = 25, dI_G/dt = 1A/\mu s$	10	V
dv/dt	Critical Rate of Rise on-State Voltage,min.	$T_j = 125, V_D = \frac{2}{3}V_{DRM}$, Exponential wave.	50	V/ μs
$(dv/dt)_c$	Critical Rate of Rise off-State Voltage at commutation, min	$T_j = 125, V_D = \frac{2}{3}V_{DRM}, (dv/dt)_c = 15A/ms$	6	V/ μs
I_H	Holding Current, typ.	$T_j = 25$	30	mA
$R_{th(j-c)}$	Thermal Impedance, max	Junction to case	1.6	/W

